

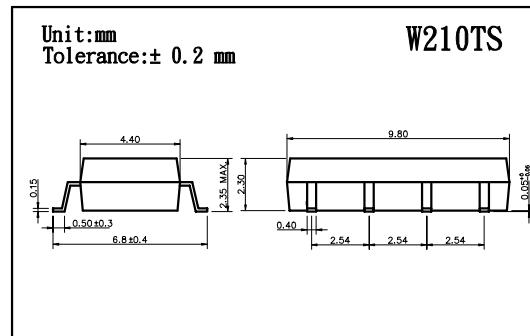
W210TS

HIGH VOLTAGE, PHOTO MOS RELAY

COSMO

FEATURES

- Photo Mos Relay and Optocoupler in One Package
- Control 350VAC or DC Voltage
- Switch 130mA Loads
- LED control Current, 5mA
- Low ON-Resistance
- dv/dt, >500V/ms
- Isolation Test Voltage, 1500VACrms



Absolute Maximum Ratings(Ta=25°C)

Emitter(Input)

Reverse Voltage	5.0V
Continuous Forward Current	50mA
Peak Forward Current	1A
Power Dissipation	100mW
Derate Linearly from 25°C	1.3mW/°C

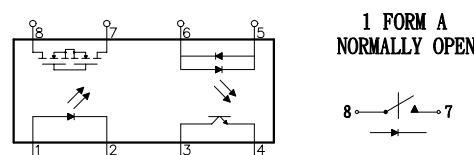
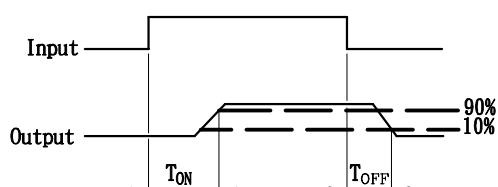
Detector(Output)

Output Breakdown Voltage	± 350V
Continuous Load Current	± 130mA
Power Dissipation	500mW

General Characteristics

Isolation Test Voltage	1500VACrms
Isolation Resistance Vio=500V, Ta=25°C	$\geq 10^{10}\Omega$
Total Power Dissipation	550mW
Derate Linearly from 25°C	2.5mW/°C
Storage Temperature Range	-40°C to +125°C
Operating Temperature Range	-30°C to +85°C
Junction Temperature	100°C
Soldering Temperature, 2mm from case, 10 sec	260°C

● Turn on/Turn off time



W210TS**HIGH VOLTAGE, PHOTO E-MOS RELAY****Characterisitcs**

(Ta=25°C)

Description	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Emitter (Input)						
Forward Voltage	VF		1.2	1.5	V	IF=10mA
Operation Input Current	IFON			5	mA	VL=± 20V, IL=100mA t=10ms
Recovery Input Current	IFOFF	0.2			mA	VL=± 20V, IL<=5uA
Detector (output)						
Output Breakdown Voltage	VB	350			V	IB=50uA
Output Off-State Leakage	IT(OFF)		0.2	1	uA	VT=100V, IF=0mA
I/O Capacitance	CISO		6		pF	IF=0, f=1MHz
ON Resistance	RON		20	30	Ω	IL=100mA, IF=10mA
Turn-on Time	TON		0.3	1.0	ms	IF=10mA, VL=± 20V
Turn-off Time	TOFF		0.7	1.5	ms	t=10ms, IL=± 100mA

Mos Relay Schematic and Wiring Diagrams

Type	Schematic	Output configuration	Load	Con-nection	Wiring Diagrams
W210TS		1a	AC/DC	-	

DATA CURVE

Load current vs. ambient temperature

Allowable ambient temperature:

-40°C to +85°C

On resistance vs. ambient temperature

Across terminals 7 and 8 pin

LED current: 5mA

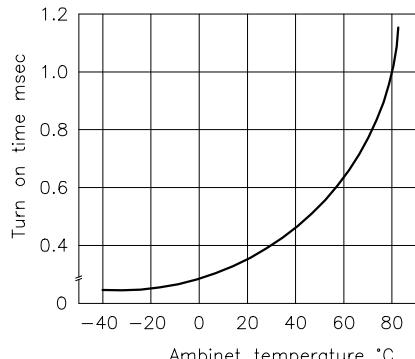
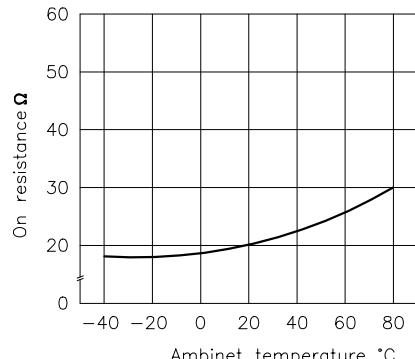
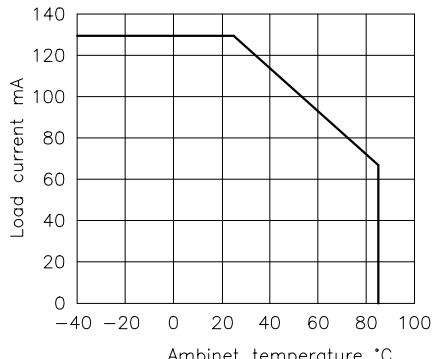
Continuouse load current: 130mA(DC)

Trun on time vs. ambient temperature

Load voltage 400V(DC)

LED current: 5mA

Continuouse load current: 130mA(DC)



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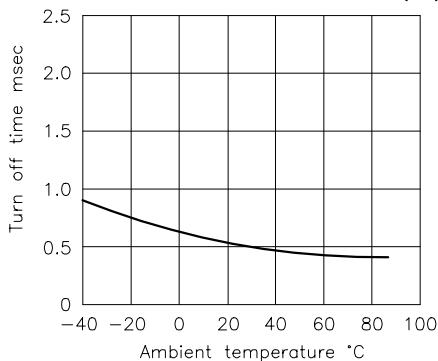
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Turn off time vs. ambient temperature
LED current: 5mA

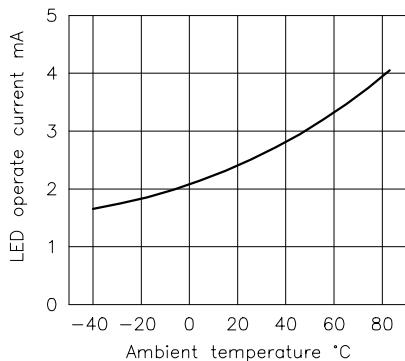
Load voltage: 400V(DC)

Continuous load current: 130mA(DC)



LED operate vs. ambient temperature
Load voltage: 400V(DC)

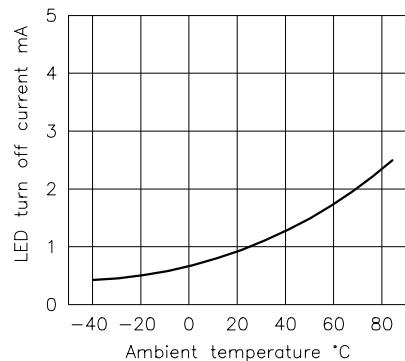
Continuous load current: 130mA(DC)



LED turn off current vs. ambient temperature

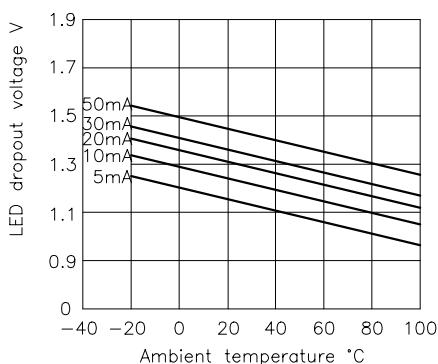
Load voltage: 400V(DC)

Continuous load current: 130mA(DC)

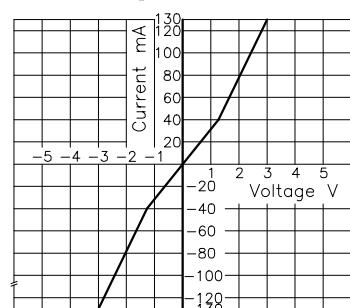


LED dropout voltage vs. ambient temperature

LED current: 5 to 50mA

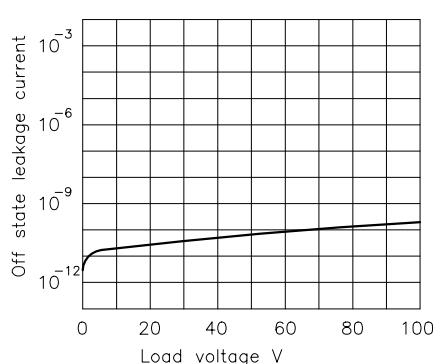


Voltage vs. current characteristics of output at MOS FET portion
Measured portion: across terminal 7 and 8 pin
Ambient temperature: 25°C

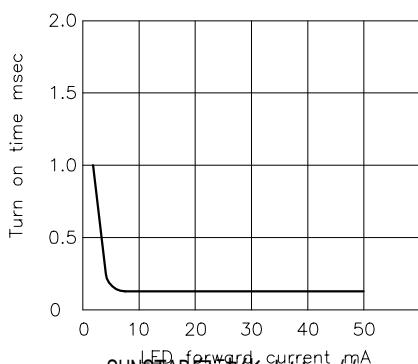


Off state leakage current
Across terminals 7 and 8 pin

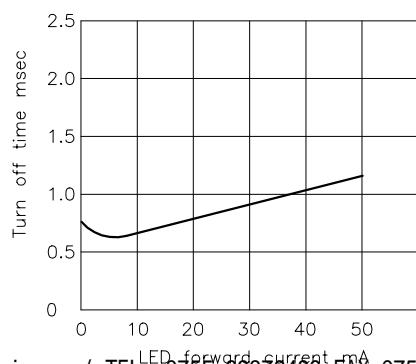
Ambient temperature: 25°C



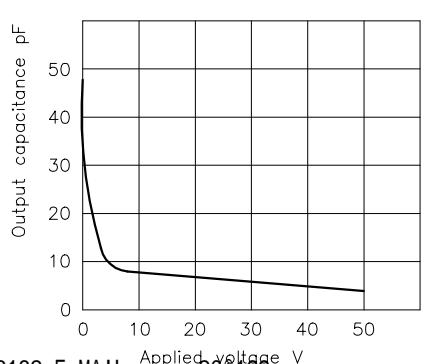
LED forward current vs. turn on time
Across terminals 7 and 8 pin
load voltage: 400V(DC); Continuous load current: 130mA(DC); Ambient temperature: 25°C



LED forward current vs. turn off time
Across terminals 7 and 8 pin
load voltage: 400V(DC); Continuous load current: 130mA(DC); Ambient temperature: 25°C



Applied voltage vs. output capacitance
Across terminals 7 and 8 pin
Frequency: 1MHz; Ambient temperature 25°C



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● Absolute Maximum Ratings

(Ta=25°C)

Parameter		Symbol	Rating	Unit
Input	Forward current	I _F	± 50	mA
	Peak forward current	I _{FM}	± 1	A
	Power dissipation	P _D	70	mW
Output	Collector-emitter voltage	V _{C EO}	60	V
	Emitter-collector voltage	V _{EC O}	6	V
	Collector current	I _c	50	mA
	Collector power dissipation	P _c	150	mW
Total power dissipation		P _{tot}	200	mW
Isolation voltage 1 minute		V _{iso}	1500	V _{rms}
Operating temperature		T _{opr}	-30 to +100	° C
Storage temperature		T _{tsg}	-55 to +125	° C
Soldering temperature 10 second		T _{sol}	260	° C

● Electro-optical Characteristics

(Ta=25°C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input	Forward voltage	V _F	I _F =± 20mA	-	1.2	1.4	V
	Peak forward voltage	V _{FM}	I _{FM} =± 0.5A	-	-	3.5	V
Output	Terminal capacitance	C _t	V=0, f=1kHz	-	30	-	pF
	Collector dark current	I _{CEO}	V _{CE} =20V, I _F =0	-	-	0.1	uA
	Current transfer ratio	CTR	I _F =± 1mA, V _{CE} =5V	30	100	-	%
	Collector-emitter saturation voltage	V _{CE(sat)}	I _F =± 20mA, I _c =1mA	-	0.1	0.3	V
	Isolation resistance	R _{iso}	DC500V	5x10 ¹⁰	10 ¹¹	-	ohm
	Floating capacitance	C _f	V=0, f=1MHz	-	0.6	1.0	pF
	Cut-off frequency	f _c	V _{CC} =5V, I _c =2mA, R _L =100ohm	-	80	-	kHz
	Response time (Rise)	t _r	V _{CC} =2V, I _c =2mA, R _L =100ohm	-	5	20	us
	Response time (Fall)	t _f		-	4	20	us

Fig.1 Current Transfer Ratio vs. Forward Current

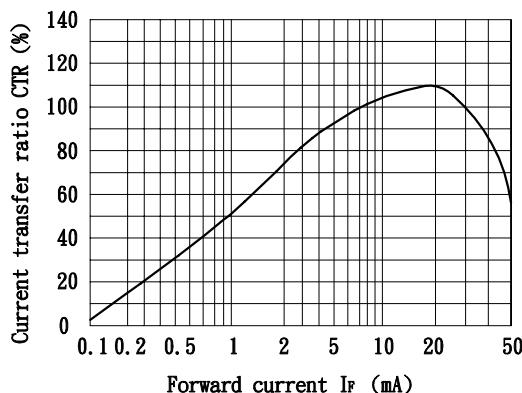
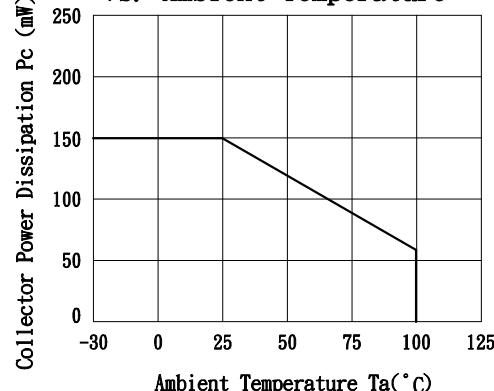


Fig. 2 Collector Power Dissipation vs. Ambient Temperature



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Fig. 3 Collector Dark Current vs. Ambient Temperature

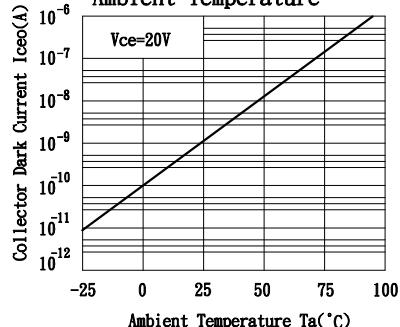


Fig. 4 Forward Current vs. Ambient Temperature

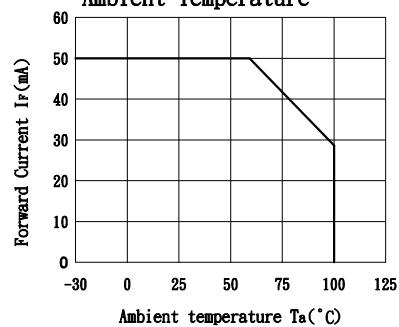


Fig. 5 Forward Current vs. Forward Voltage

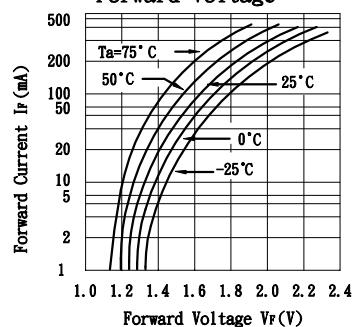


Fig. 6 Collector Current vs. Collector-emitter Voltage

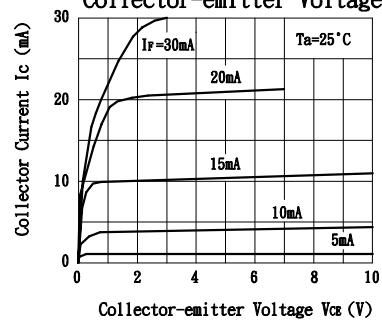


Fig. 7 Relative Current Transfer Ratio vs. Ambient Temperature

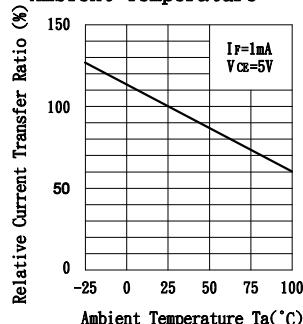


Fig. 8 Collector-emitter Saturation Voltage vs. Ambient Temperature

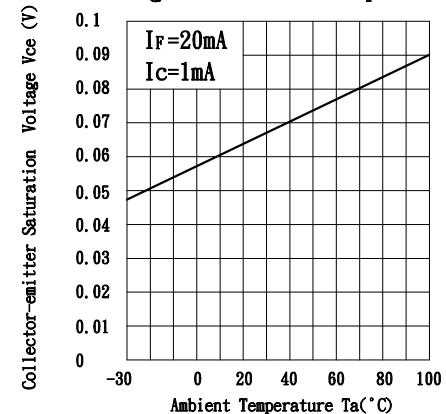


Fig. 9 Collector-emitter Saturation Voltage vs. Forward Current

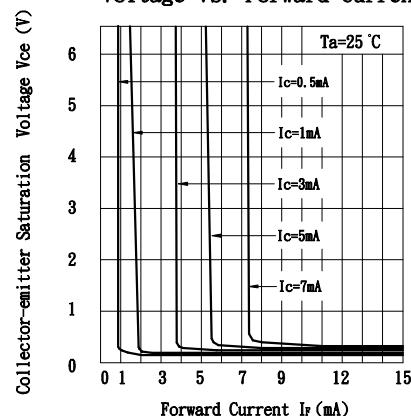


Fig. 10 Response Time vs. Load Resistance

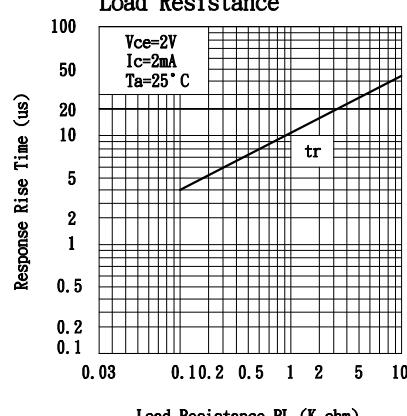


Fig. 11 Response Time vs. Load Resistance

